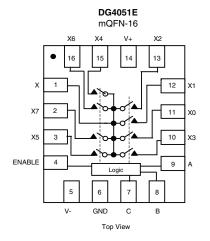
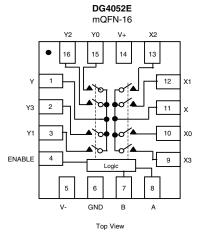
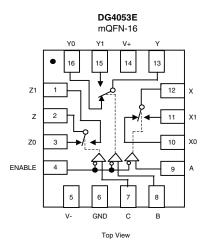


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FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION









 $\begin{array}{ll} \text{Device Marking: } \underline{Fxx} \text{ for DG4051E} \\ \text{(miniQFN16)} & \underline{G}xx \text{ for DG4052E} \\ \underline{H}xx \text{ for DG4053E} \\ xx = \text{Date/Lot Traceability Code} \end{array}$

TRUTH T	TRUTH TABLE										
ENABLE		SELECT INPUTS		ON SWITCHES							
INPUT	С	СВ		DG4051E	DG4052E	DG4053E					
Н	Х	Х	Х	All switches open	All switches open	All switches open					
L	L	L	L	X to X0	X to X0, Y to Y0	X to X0, Y to Y0, Z to Z0					
L	L	L	Н	X to X1	X to X1, Y to Y1	X to X1, Y to Y0, Z to Z0					
L	L	Н	L	X to X2	X to X2, Y to Y2	X to X0, Y to Y1, Z to Z0					
L	L	Н	Н	X to X3	X to X3, Y to Y3	X to X1, Y to Y1, Z to Z0					
L	Н	L	L	X to X4	X to X0, Y to Y0	X to X0, Y to Y0, Z to Z1					
L	Н	L	Н	X to X5	X to X1, Y to Y1	X to X1, Y to Y0, Z to Z1					
L	Н	Н	L	X to X6	X to X2, Y to Y2	X to X0, Y to Y1, Z to Z1					
L	Н	Н	Н	X to X7	X to X3, Y to Y3	X to X1, Y to Y1, Z to Z1					

ORDERING INFORM	ATION			
TEMPERATURE RANGE	CONFIGURATION	PACKAGE	PART NUMBER	MIN. ORDER / PACKAGING QUANTITY
	DG4051E	16-pin TSSOP	DG4051EEQ-T1-GE3	Tape and reel 3000 units
		16-pin SOIC	DG4051EEY-T1-GE3	Tape and reel 2500 units
		16-pin miniQFN	DG4051EEN-T1-GE4	Tape and reel 3000 units
40 °C + 105 °C °		16-pin TSSOP	DG4052EEQ-T1-GE3	Tape and reel 3000 units
-40 °C to +125 °C ^a Lead (Pb)-Free	DG4052E	16-pin SOIC	DG4052EEY-T1-GE3	Tape and reel 2500 units
Load (1 b) 1 100		16-pin miniQFN	DG4052EEN-T1-GE4	Tape and reel 3000 units
		16-pin TSSOP	DG4053EEQ-T1-GE3	Tape and reel 3000 units
	DG4053E	16-pin SOIC	DG4053EEY-T1-GE3	Tape and reel 2500 units
		16-pin miniQFN	DG4053EEN-T1-GE4	Tape and reel 3000 units

Note

a. -40 °C to +85 °C datasheet limits apply.

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ABSOLUTE MAXIMUM RA	TINGS ($T_A = 25 ^{\circ}\text{C}$, unless otherw	vise noted)		
PARAMETER		LIMIT	UNIT	
V+ to V-		-0.3 to +18		
GND to V-		-18	V	
Digital Inputs ^a , V _S , V _D		(V-) - 0.3 to (V+) + 0.3 or 30 mA, whichever occurs first		
Continuous Current (any terminal)		30	mA	
Peak Current, S or D (pulsed 1 ms, 1	0 % duty cycle)	100	IIIA	
Storage Temperature		-65 to +150	°C	
	16-pin TSSOP ^c	450		
Power Dissipation ^b	16-pin miniQFN ^{d, f}	525	mW	
	16-pin narrow SOIC ^e	640		
	16-pin TSSOP ^c	178		
Thermal Resistance b	16-pin miniQFN ^{d, f}	152	°C/W	
	16-pin narrow SOIC ^e	125		
ESD Human Body Model (HBM); per	ANSI / ESDA / JEDEC® JS-001	2500	V	
Latch Up Current, per JESD78D		400	mA	

Notes

- a. Signals on SX, DX, or INX exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 5.6 mW/°C above 70 °C.
- d. Derate 6.6 mW/°C above 70 °C.
- e. Derate 8.0 mW/°C above 70 °C.
- f. Manual soldering with iron is not recommended for leadless components. The miniQFN-16 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper lip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

SPECIFICATIONS	SPECIFICATIONS FOR DUAL SUPPLIES									
		TEST CONDITIONS			-40 °C to +125 °C		-40 °C to +85 °C			
PARAMETER	SYMBOL	UNLESS OTHERWISE SPECIFIED $V+=5~V,~V-=-5~V$ $V_{IN(A,~B,~C,~and~enable)}=2~V,~0.8~V$ a	TEMP. b	TYP. °	MIN. d	MAX. d	MIN. d	MAX. d	UNIT	
Analog Switch										
Analog Signal Range e	V _{ANALOG}		Full	-	-5	5	-5	5	V	
On-Resistance	D	$I_S = 1 \text{ mA}, V_D = -3 \text{ V}, 0 \text{ V}, 3 \text{ V}$	Room	68	-	78	-	78		
On-nesistance	R _{ON}	ig = 1 IIIA, VD = -3 V, U V, 3 V	Full	-	ı	106	-	97		
On-Resistance Match	۸D	ΔR_{ON} $I_S = 1 \text{ mA}, V_D = \pm 3 \text{ V}$		0.91	-	6	-	6	Ω	
On-nesistance materi	ΔΠΟΝ	$I_S = I IIIA, V_D = \pm 3 V$	Full	-	-	6	-	6	32	
On-Resistance	D	Is = 1 mA. V _D = -3 V. 0 V. 3 V	Room	10	-	17	-	17		
Flatness	R _{FLATNESS}	$I_S = I IIIA, V_D = -3 V, U V, 3 V$	Full	-	-	20	-	19		
	l		Room	± 0.05	-1	1	-1	1		
Switch Off	I _{S(off)}	V+ = 5.5 V, V- = -5.5 V,	Full	-	-50	50	-5	5	- nA	
Leakage Current	1	$V_D = \pm 4.5 \text{ V}, V_S = \mp 4.5 \text{ V}$	Room	± 0.05	-1	1	-1	1		
	I _{D(off)}		Full	-	-50	50	-5	5		
Channel On		V+ = 5.5 V, V- = -5.5 V,	Room	± 0.05	-1	1	-1	1		
Leakage Current	I _{D(on)}	$V_S = V_D = \pm 4.5 \text{ V}$	Full	-	-50	50	-5	5		
Digital Control										
Input Current, V _{IN} Low	I _{IL}	$V_{IN(A,\ B,\ C,\ and\ enable)}$ under test = 0.6 V	Full	0.02	-1	1	-1	1		
Input Current, V _{IN} High	I _{IH}	V _{IN(A, B, C, and enable)} under test = 2 V	Full	0.02	-1	1	-1	1	μA	
Input Capacitance e	C _{IN}	f = 1 MHz	Room	3.4	-	-	-	-	pF	



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		TEST CONDIT	-			-40 °C to	+125 °C	-40 °C to +85 °C		
PARAMETER	SYMBOL	UNLESS OTHERWISE SPECIFIED V+ = 5 V, V- = -5 V		TEMP. b	TYP. c	MIN. d	MAX. d	MIN. d	MAX. d	UNIT
		$V_{IN(A, B, C, and enable)} = 2 V, 0.8 V^a$								
Dynamic Characterist	ics									
			f = 100 kHz	Room	-106	-	-	-	-	
Off Isolation e	OIRR		f = 10 MHz	Room	-68	-	-	-	-	
		$R_L = 50 \Omega$, $C_L = 1 pF$	f = 100 MHz	Room	-49	-	ı	-	ı	dB
01 11 01 1		nt = 30 32, Ot = 1 pr	f = 100 kHz	Room	-105	-	ı	-	ı	uв
Channel-to-Channel Crosstalk e	X_{TALK}		f = 10 MHz	Room	-62	-	-	-	-	
O O O O O O O O O O O O O O O O O O O			f = 100 MHz	Room	-51	-	-	-	-	
			DG4051E	Room	308	-	-	-	-	
Bandwidth, 3 dB	BW	$R_L = 50 \Omega$	DG4052E	Room	353	-	-	-	-	MHz
			DG4053E	Room	930	-	-	-	-	
Transition Time				Room	72	-	112	-	112	
Transition Time	t _{TRANS}			Full	-	-	139	-	131	
Facility of Oak		$R_L = 300 \Omega, C_L = 35 pF$		Room	35	-	75	-	75	
Enable Turn-On Time	t _{ON}			Full	-	-	86	-	80	
5 II 5 0" F		see Fig. 1, 2	2, 3	Room	48	-	88	-	88	ns
Enable Turn-Off Time	t _{OFF}			Full	-	-	97	-	95	
Break-Before-Make			Room	-	1	-	1	-		
Time Delay	t _D			Full	-	-	-	-	-	<u> </u>
Charge Injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega,$	C _L = 1 nF	Room	0.38	-	-	-	-	рС
			DG4051E	Room	2.2	-	-	-	-	
Source Off	C _{S(off)}	f = 1 MHz	DG4052E	Room	2.1	-	-	-	-	
Capacitance e	93(011)		DG4053E	Room	2	-	-	-	-	1
			DG4051E	Room	9.2	-	-	-	-	
Drain Off	C _{D(off)}	f = 1 MHz	DG4052E	Room	4.8	-	-	-	-	pF
Capacitance e	= (0)		DG4053E	Room	3.1	-	-	-	-	1
			DG4051E	Room	14.9	-	-	-	-	
Channel On	C _{D(on)}	f = 1 MHz	DG4052E	Room	10	-	-	-	-	
Capacitance e	2(0.1)		DG4053E	Room	8.5	-	-	-	-	
Total Harmonic Distortion ^e	THD	Signal = 5 V _I 20 Hz to 20 kHz, F		Room	0.065	-	-	-	-	%
Power Supplies										
D 0 10 1				Room	0.05	-	1	-	1	
Power Supply Current	I+			Full	-	-	10	-	10	
Negative Supply		V+ = 5 V, V- =	5 V	Room	-0.05	-1	-	-1	-	1 .
Current	I-	V+ = 5 V, V- = -5 V V _{IN(A, B, C, and enable)} = 0 V or 5 V		Full	-	-10	-	-10	-	μA
	I _{GND}	my, b, c, and shade)		Room	-0.05	-1	-	-1	-	
round Current				Full	-	-10	_	-10	_	1



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		TEST CONDIT	FIONS			-40 °C to	o +125 °C	-40 °C t	.o +85 °C	
PARAMETER	SYMBOL	V+ = 12 V, V-	= 0 V	TEMP. b	TYP. °	MIN. d	MAX. d	MIN. d	MAX. d	UNI
Analog Switch		V _{IN(A, B, C, and enable)} =	: 2 V, U.O V ~							
Analog Switch Analog Signal Range e	V			Full		0	12	0	12	V
Analog Signal hange	V _{ANALOG}			Room	85	-	103	-	103	_ v
On-Resistance	R _{ON}	$I_S = 1 \text{ mA}, V_D = 0.7 \text{ V}, 11.3 \text{ V}$		Full	-	_	133	-	125	
				Room	1.24	-	8	-	8	•
On-Resistance Match	ΔR_{ON}	$I_S = 1 \text{ mA}, V_D =$: 11.3 V	Full	-	-	8	-	8	Ω
On-Resistance	D	1 - 1 m \ \/ - 0 -	7 \/ 11 2 \/	Room	27	-	37	-	37	
Flatness	R _{FLATNESS}	$I_S = 1 \text{ mA}, V_D = 0.7$	7 V, 11.3 V	Full	-	-	44	-	43	
	1			Room	± 0.05	-1	1	-1	1	
Switch Off	I _{S(off)}	V+ = 13.2 V, V		Full	-	-50	50	-5	5	
Leakage Current		$V_D = 1 V / 12.2 V, V_S = 10$	= 12.2 V / 1 V	Room	± 0.05	-1	1	-1	1	nA
	I _{D(off)}			Full	-	-50	50	-5	5	11/-
Channel On		V+ = 13.2 V, V	- = 0 V	Room	± 0.05	-1	1	-1	1	
Leakage Current	I _{D(on)}	$V_D = V_S = 1 \text{ V}$	12.2 V	Full	-	-50	50	-5	5	
Digital Control										
Input Current, V _{IN} Low	l∟	V _{IN(A, B, C, and enable)} under test = 0.8 V		Full	0.02	-1	1	-1	1	μÆ
Input Current, V _{IN} High	Ι _Η	$V_{IN(A, B, C, and enable)}$ under test = 2 V		Full	0.02	-1	1	-1	1	μ
Dynamic Characteristi	ics									
Transition Time	t		Room	43	-	83	-	83		
Transition fine	t _{TRANS}		Full	-	-	95	-	90		
Enable Turn-On Time	+	$R_L = 300 \ \Omega, \ C_L = 35 \ pF$ see Fig. 1, 2, 3		Room	22	-	62	-	62	
Litable fulli-Off fillie	t _{ON}			Full	-	-	71	-	67	n
Enable Turn-Off Time	torr			Room	47	-	87	-	87] ''
Lilable Tulli-Oli Tillie	t _{OFF}			Full	-	-	94	-	93	
Break-Before-Make	t _D			Room	25	1	-	1	-	
Time Delay	טי			Full	-	-	-	-	-	
Charge Injection ^e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega$, C _L = 1 nF	Full	-	-	-	-	-	р
Off Isolation ^e	OIRR	$R_L = 50 \Omega, C_L$	– 1 nF	Room	-	-	-	-	-	
Channel-to-Channel Crosstalk ^e	X _{TALK}	f = 100 kH		Room	-	-	-	-	-	d
0.00			DG4051E	Room	-	-	-	-	-	
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz	DG4052E	Room	-	-	-	-	-	
o a paoriano o			DG4053E	Room	-	-	-	-	-	
D : 0"			DG4051E	Room	-	-	-	-	-	
Drain Off Capacitance ^e	$C_{D(off)}$	f = 1 MHz	DG4052E	Room	-	-	-	-	-	р
oupuo.iui.oo			DG4053E	Room	-	-	-	-	-	
01			DG4051E	Room	-	-	-	-	-	
Channel On Capacitance ^e	C _{D(on)}	f = 1 MHz	f = 1 MHz DG4052E		-	-	-	-	-	
		DG4053E		Room	-	-	-	-	-	
Power Supplies						1	1			
Power Supply Current	l+			Room Full	0.05	-	1 10	-	1 10	-
Negative Supply			Room	-0.05	-1	-	-1	-	İ	
Negative Supply Current	l-	$V_{IN(A,\;B,\;C,\;and\;enable)}$:	= 0 V or 5 V	Full	-	-10	_	-10	_	μ
		Room	-0.05	-10	_	-10	-	1		
Ground Current	I_{GND}	-		Full	0.00	<u> </u>		<u> </u>		1



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		TEST CONDI	TIONS			-40 °C to +125 °C		-40 °C to +85 °C		
PARAMETER	SYMBOL	V+ = 5 V, V-	= 0 V	TEMP. b	TYP. c	MIN. d	MAX. d	MIN. d	MAX. d	UNI
Amalan Corital		V _{IN(A, B, C, and enable)} =	= 2 V, U.8 V ª							
Analog Switch	.,			I - "	1				I -	
Analog Signal Range ^e	V _{ANALOG}			Full	-	0	5	0	5	V
On-Resistance	R _{ON}	$I_S = 1 \text{ mA}, V_D = 0 \text{ V}, 3.5 \text{ V}$		Room Full	125	-	147 176	-	147 168	
				Room	1.3	-	8	-	8	
On-Resistance Match	ΔR_{ON}	$I_S = 1 \text{ mA}, V_D = 1 \text{ mA}$	= 3.5 V	Full	-	-	8	-	8	Ω
On-Resistance	Б	1 4 1	0.1/. 0.1/	Room	21	-	31	-	31	
Flatness	R _{FLATNESS}	$I_S = 1 \text{ mA}, V_D =$	0 V, 3 V	Full	-	-	25	-	29	
					± 0.03	-1	1	-1	1	
Switch Off	I _{S(off)}	V+ = 5.5 V, V-	= 0 V	Full	-	-50	50	-5	5	
Leakage Current		$V_D = 1 \text{ V} / 4.5 \text{ V}, V_S$	= 4.5 V / 1 V	Room	± 0.03	-1	1	-1	1	
	I _{D(off)}			Full	-	-50	50	-5	5	n/
Channel On		V+ = 5.5 V, V-	= 0 V	Room	± 0.03	-1	1	-1	1	
Leakage Current	I _{D(on)}	$V_D = V_S = 1 V$	/ 4.5 V	Full	-	-50	50	-5	5	
Digital Control										
Input Current, V _{IN} Low	ΙL	V _{IN(A, B, C, and enable)} under test = 0.6 V		Full	0.02	-1	1	-1	1	μA
Input Current, V _{IN} High	I _H	V _{IN(A, B, C, and enable)} under test = 2 V		Full	0.02	-1	1	-1	1	μ
Dynamic Characterist	ics									
Transition Time	+			Room	95	-	135	-	135	
Transition time	t _{TRANS}		Full	-	-	169	-	148		
Enable Turn-On Time	+	$R_L = 300 \ \Omega, \ C_L = 35 \ pF$ see Fig. 1, 2, 3		Room	56	-	96	-	96	
Lilable fulli-Oli fillie	t _{ON}			Full	-	-	117	-	107	ns
Enable Turn-Off Time	torr			Room	55	-	95	-	95	116
Lilable fulli-Oli fillie	t _{OFF}			Full	-	-	110	-	103	
Break-Before-Make	t _D			Room	-	12	-	12	-	
Time Delay	טי			Full	-	-	-	-	-	
Charge Injection ^e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega$, C _L = 1 nF	Full	0.32	-	-	-	-	р
Off Isolation ^e	OIRR	$R_L = 50 \Omega, C_L$	– 1 nF	Room	-86	-	-	-	-	
Channel-to-Channel Crosstalk ^e	X _{TALK}	f = 100 kH		Room	-105	-	-	-	-	dl
2 2"			DG4051E	Room	2.4	-	-	-	-	
Source Off Capacitance ^e	C _{S(off)}	f = 1 MHz	DG4052E	Room	2.4	-	-	-	=.	
Sapastarioc			DG4053E	Room	2.3	-	-	-	-	
			DG4051E	Room	10.1	-	-	-	-	
Drain Off Capacitance ^e	C _{D(off)}	f = 1 MHz	DG4052E	Room	5.3	-	-	-	-	р
capacitarios			DG4053E	Room	3.4	-	-	-	-	
01			DG4051E	Room	15.9	-	-	-	-	
Channel On Capacitance ^e	C _{D(on)}	f = 1 MHz DG4052E		Room	10.6	-	-	-	-	
		DG4053E		Room	8.9	-	-	-	-	
Power Supplies	1					1	ı	ı		
Power Supply Current	I+			Room	0.05	-	1 10	-	10	-
			Full	0.05		10		10		
Negative Supply Current	I-	V _{IN(A, B, C, and enable)}	= 0 V or 5 V	Room	-0.05	-1	-	-1 10	_	μΑ
Curront		וויקרי, ט, ט, מווט פוומטוס)		Full Room	-0.05	-10 -1	-	-10 -1	-	1
	rrent I _{GND}									

S16-0623-Rev. A, 11-Apr-16

Document Number: 69685



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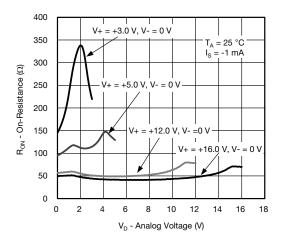
		TEST CONDI	TIONS			-40 °C to	o +125 °C	-40 °C t	:o +85 °C	
PARAMETER	SYMBOL	UNLESS OTHERWIS		TEMP. b	TYP. °					UN
		$V+=3 V, V-V_{IN(A, B, C, and enable)} = 0$				MIN. d	MAX. d	MIN. d	MAX. d	
Analog Switch		· IN(A, B, C, and enable)	,							
Analog Signal Range e	V _{ANALOG}			Full	_	0	3	0	3	V
7a.og	ANALOG			Room	221	-	-	-	-	
On-Resistance	R _{ON}	$I_S = 1 \text{ mA}, V_D = 1 \text{ mA}$	= 1.5 V	Full		_	_	_	_	2
				Room	± 0.02	-1	1	-1	1	
Switch Off	I _{S(off)}	V+ = 3.3 V, V-	- 0 V	Full	-	-50	50	-5	5	
Leakage Current		$V_D = 0.3 \text{ V} / 3 \text{ V}, V_S$		Room	± 0.02	-1	1	-1	1	
· ·	I _{D(off)}			Full	-	-50	50	-5	5	n.
Channel On		V ₁ = 2.2 V V	- 0 V	Room	± 0.02	-1	1	-1	1	
Leakage Current	I _{D(on)}	V+ = 3.3 V, V- = 0 V $V_D = V_S = 0.3 \text{ V} / 3 \text{ V}$		Full		-50	50	-5	5	
Digital Control				ı un		00	00			
	1 .	V _{IN(A, B, C, and}	onablo)				<u> </u>		<u> </u>	
Input Current, V _{IN} Low	ΙL	under test =	0.6 V	Full	0.02	-1	1	-1	1	
Input Current, V _{IN} High	I _H	V _{IN(A, B, C, and}	enable)	Full	0.02	-1	1	-1	1	μ
		under test = 1.4 V		I uii	0.02	-1	'	'_	'	
Dynamic Characterist	ics				T	ı	ı	1	1	
Transition Time	t _{TRANS}		Room	200	-	-	-	-		
Transition Time	TRANS		Full	-	-	-	-	-		
Enable Turn-On Time	ton	$R_L = 300 \ \Omega, \ C_L = 35 \ pF$ see Fig. 1, 2, 3		Room	130	-	-	-	-	
Litable rain on nine	UN			Full	-	-	-	-	-	n
Enable Turn-Off Time	t			Room	78	-	-	-	-	
Lilable fulli-Oil fillie	t _{OFF}			Full	-	-	-	-	-	1
Break-Before-Make				Room	130	-	-	-	-	
Time Delay	t _D			Full	-	-	-	-	-	
Charge Injection e	Q	$V_g = 0 \text{ V}, R_g = 0 \Omega$, C _L = 1 nF	Room	0.34	-	-	-	=.	р
Off Isolation e	OIRR	D 5000	1	Room	-88	-	-	-	-	
Channel-to-Channel Crosstalk ^e	X _{TALK}	$R_L = 50 \Omega, C_L$ f = 100 kH	= i pr Iz	Room	-105	-	-	-	-	dl
			DG4051E	Room	2.6	-	-	-	-	
Source Off Capacitance e	C _{S(off)}	f = 1 MHz	DG4052E	Room	2.6	-	-	-	-	
Capacitance -			DG4053E	Room	2.5	-	-	-	-	
			DG4051E	Room	10.7	-	-	-	-	
Drain Off Capacitance e	C _{D(off)}	f = 1 MHz	DG4052E	Room	5.7	-	-	-	-	р
	(*)		DG4053E	Room	3.6	-	-	-	-	
			DG4051E	Room	16.4	-	-	-	-	
Channel On	C _{D(on)}	f = 1 MHz	DG4052E	Room	10.9	-	-	-	-	1
Capacitance e	5(011)		DG4053E	Room	9.1	-	-	-	-	
Power Supplies	l				II.					
				Room	0.05	_	1	l -	1	
Power Supply Current	I+			Full	-	-	10	-	10	1
Negative Supply				Room	-0.05	-1	-	-1	-	1
Current	I-	V _{IN(A, B, C, and enable)}	= 0 V or 3 V	Full	-	-10	_	-10	_	μ
	I _{GND}	,		Room	-0.05	-1	_	-1	_	1
Ground Current				Full		-10	_	-10	-	
	l .			i uii		-10	L	-10	L	

S16-0623-Rev. A, 11-Apr-16

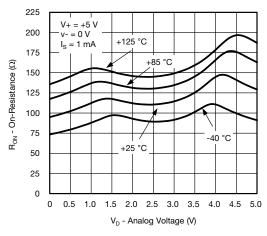
- a. V_{IN} = input voltage to perform proper function. b. Room = 25 °C, full = as determined by the operating temperature suffix. c. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
- d. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
- e. Guaranteed by design, not subject to production test.

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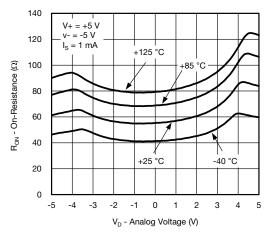
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



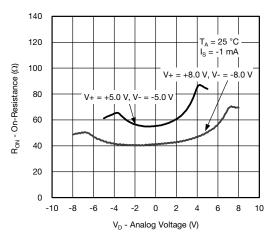
On-Resistance vs. Analog Voltage (Single Supply)



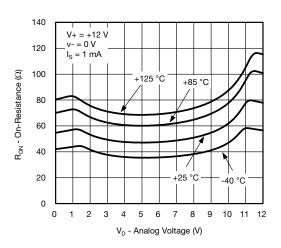
On-Resistance vs. Analog Voltage (Temperature)



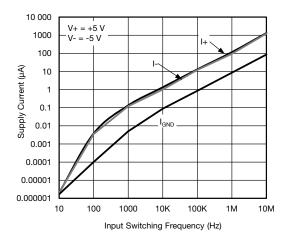
On-Resistance vs. Analog Voltage (Temperature)



On-Resistance vs. Analog Voltage (Dual Supply)



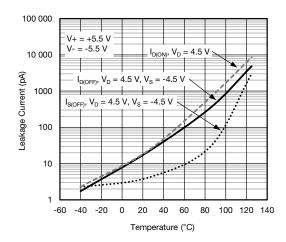
On-Resistance vs. Analog Voltage (Temperature)



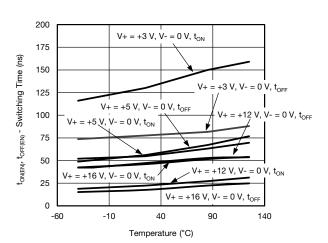
Supply Current vs. Input Switching Frequency

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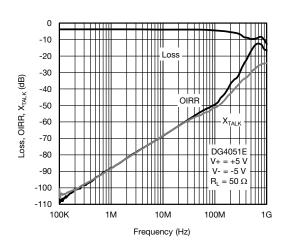
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



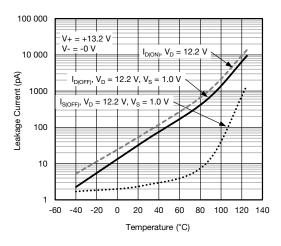
Leakage Current vs. Temperature



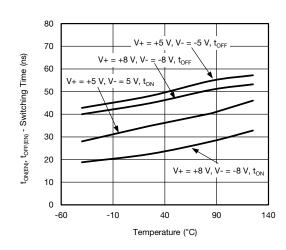
Switching Time vs. Temperature (Single Supply)



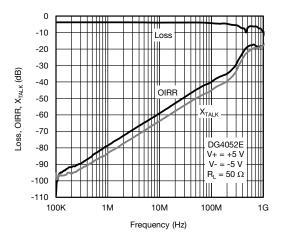
DG4051E Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



Leakage Current vs. Temperature



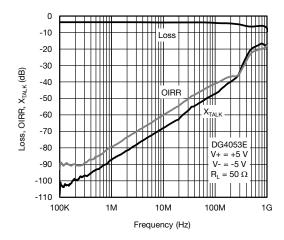
Switching Time vs. Temperature (Dual Supply)



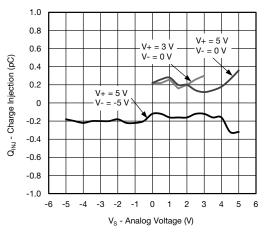
DG4052E Insertion Loss, Off-Isolation, Crosstalk vs. Frequency

Vishay Siliconix

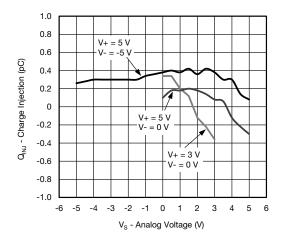
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



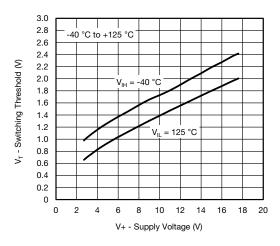
DG4053E Insertion Loss, Off-Isolation, Crosstalk vs. Frequency



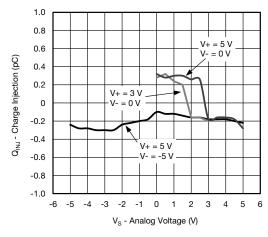
DG4051E Charge Injection vs. Analog Voltage



DG4052E Charge Injection vs. Analog Voltage

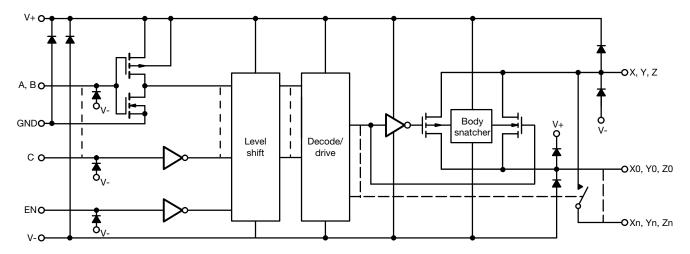


Switching Threshold vs. V+ Supply Voltage

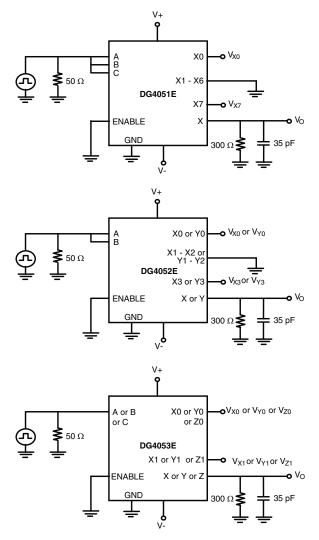


DG4053E Charge Injection vs. Analog Voltage

SCHEMATIC DIAGRAM (Typical Channel)



TEST CIRCUITS



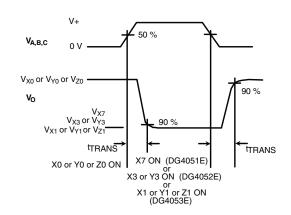
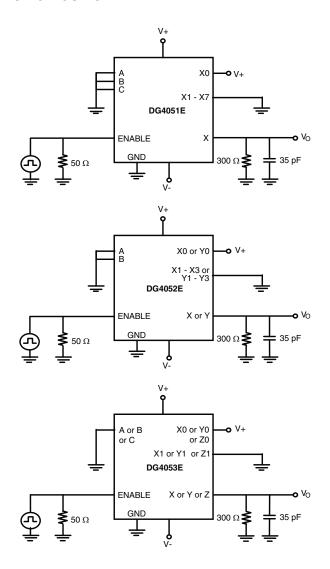


Fig. 1 - Transition Time

TEST CIRCUITS



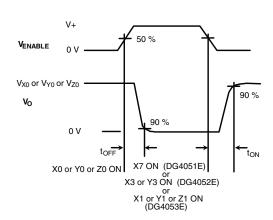


Fig. 2 - Enable Switching Time

80 %

TEST CIRCUITS

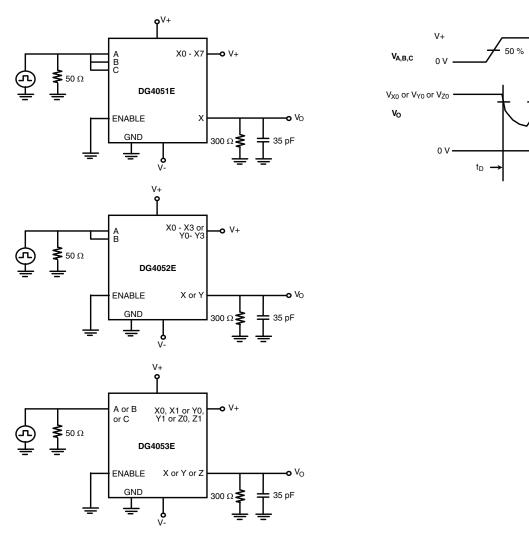


Fig. 3 - Break-Before-Make

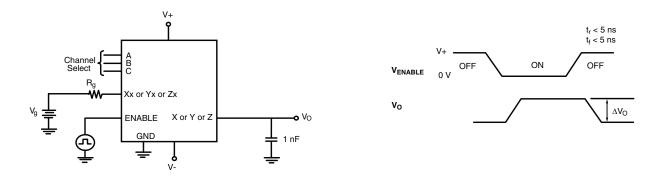


Fig. 4 - Charge Injection

TEST CIRCUITS

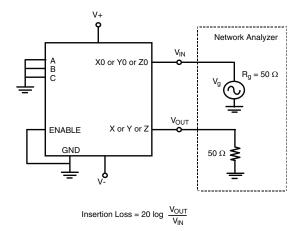


Fig. 5 - Insertion Loss

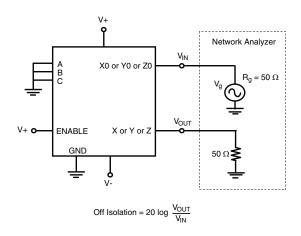


Fig. 7 - Off Isolation

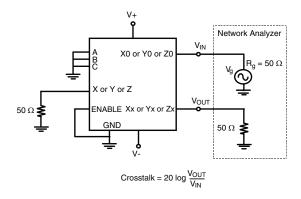


Fig. 6 - Crosstalk

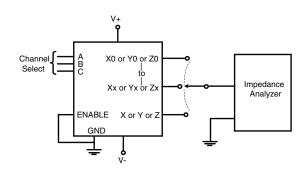
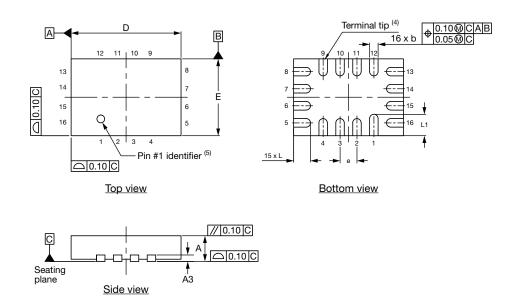


Fig. 8 - Source, Drain Capacitance

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?69685.

Thin miniQFN16 Case Outline



DIMENSIONS		MILLIMETERS (1)			INCHES		
DIMENSIONS	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
А	0.50	0.55	0.60	0.020	0.022	0.024	
A1	0	-	0.05	0	-	0.002	
A3		0.15 ref.			0.006 ref.		
b	0.15	0.20	0.25	0.006	0.008	0.010	
D	2.50	2.60	2.70	0.098	0.102	0.106	
е		0.40 BSC		0.016 BSC			
E	1.70	1.80	1.90	0.067	0.071	0.075	
L	0.35	0.40	0.45	0.014	0.016	0.018	
L1	0.45	0.50	0.55	0.018	0.020	0.022	
N ⁽³⁾	16			16			
Nd ⁽³⁾		4			4		
Ne ⁽³⁾		4		4			

Notes

- (1) Use millimeters as the primary measurement.
- (2) Dimensioning and tolerances conform to ASME Y14.5M. 1994.
- (3) N is the number of terminals. Nd and Ne is the number of terminals in each D and E site respectively.
- (4) Dimensions b applies to plated terminal and is measured between 0.15 mm and 0.30 mm from terminal tip.
- (5) The pin 1 identifier must be existed on the top surface of the package by using identification mark or other feature of package body.
- (6) Package warpage max. 0.05 mm.

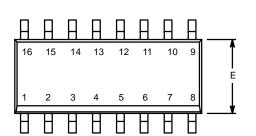
ECN: T16-0226-Rev. B, 09-May-16

DWG: 6023

Revision: 09-May-16 1 Document Number: 64694



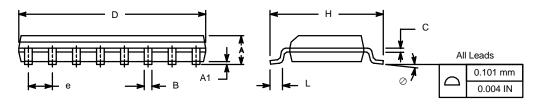
SOIC (NARROW): 16-LEAD
JEDEC Part Number: MS-012



	MILLIM	IETERS	INC	HES					
Dim	Min	Max	Min	Max					
Α	1.35	1.75	0.053	0.069					
A ₁	0.10	0.20	0.004	0.008					
В	0.38	0.51	0.015	0.020					
С	0.18	0.23	0.007	0.009					
D	9.80	10.00	0.385	0.393					
E	3.80	4.00	0.149	0.157					
е	1.27	BSC	0.050	BSC					
Н	5.80	6.20	0.228	0.244					
L	0.50	0.93	0.020	0.037					
0	0°	8°	0°	8°					
FCN: S-0	FCN: S-03946—Rev. F. 09-Jul-01								

ECN: S-03946—Rev. F, 09-Jul-01

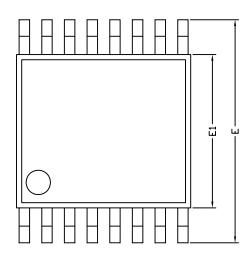
DWG: 5300

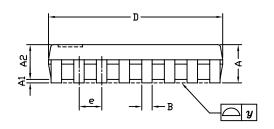


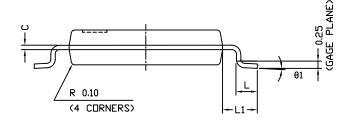
Document Number: 71194 www.vishay.com 02-Jul-01 sww.vishay.com



TSSOP: 16-LEAD







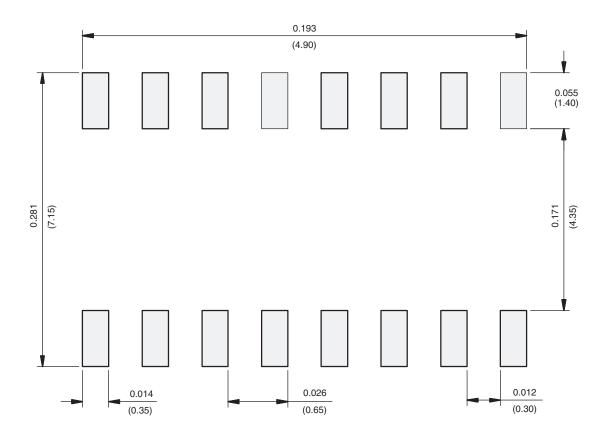
	DI	MENSIONS IN MILLIMETE	RS
Symbols	Min	Nom	Max
Α	-	1.10	1.20
A1	0.05	0.10	0.15
A2	=	1.00	1.05
В	0.22	0.28	0.38
С	=	0.127	-
D	4.90	5.00	5.10
E	6.10	6.40	6.70
E1	4.30	4.40	4.50
е	-	0.65	-
L	0.50	0.60	0.70
L1	0.90	1.00	1.10
у	=	-	0.10
θ1	0°	3°	6°
ECN: S-61920-Rev. D. 23-0	Oct-06		

DWG: 5624

Document Number: 74417 www.vishay.com 23-Oct-06



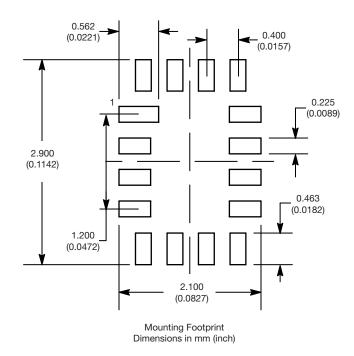
RECOMMENDED MINIMUM PAD FOR TSSOP-16



Recommended Minimum Pads Dimensions in inches (mm)



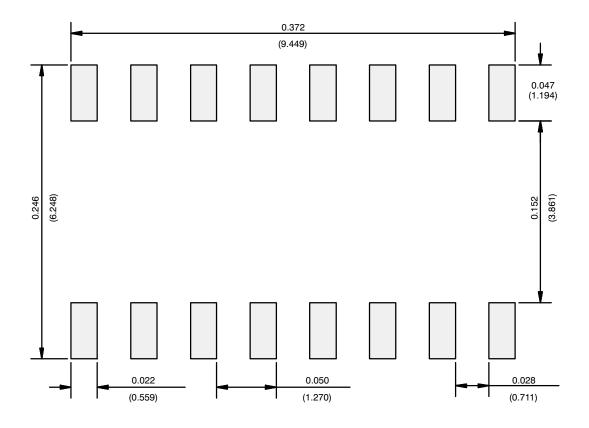
RECOMMENDED MINIMUM PADS FOR MINI QFN 16L



Revision: 05-Mar-10



RECOMMENDED MINIMUM PADS FOR SO-16



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index

APPLICATION NOTE

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Vishay

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